# RGS00TS65HR

## 650V 50A Field Stop Trench IGBT

Datasheet

V <sub>CES</sub>	650V
I <sub>C (100°C)</sub>	50A
V <sub>CE(sat) (Typ.)</sub>	1.65V
$P_D$	326W

# Outline TO-247N

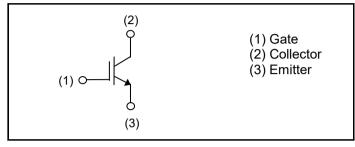
## Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Short Circuit Withstand Time 8µs
- 3) Qualified to AEC-Q101
- 4) Pb free Lead Plating; RoHS Compliant

## Application

Heater for Automotive

## ●Inner Circuit



●Packaging Specifications

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	Packaging	Tube			
	Reel Size (mm)	-			
Tuno	Tape Width (mm)	-			
Туре	Basic Ordering Unit (pcs)	450			
	Packing Code	C11			
	Marking	RGS00TS65			

# ● **Absolute Maximum Ratings** (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter  Collector - Emitter Voltage  Gate - Emitter Voltage		Symbol	Value	Unit V
		V <sub>CES</sub>	650	
		V <sub>GES</sub>	±30	V
Collector Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	88	Α
	T <sub>C</sub> = 100°C	I <sub>C</sub>	50	Α
Pulsed Collector Current	Collector Current		150	Α
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	326	W
	T <sub>C</sub> = 100°C	P <sub>D</sub>	163	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		$T_{stg}$	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>imax.</sub>

## ●Thermal Resistance

Parameter	Symbol	Values			Unit
raiailletei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	ı	0.46	°C/W

# ●IGBT Electrical Characteristics (at T<sub>i</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Linit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	-	-	V
		$V_{CE} = 650V, V_{GE} = 0V,$				
Collector Cut - off Current	I <sub>CES</sub>	$T_j = 25^{\circ}C$ $Tj = 175^{\circ}C^{*2}$	-	-	10	μΑ
		Tj = 175°C <sup>*2</sup>	-	-	5	mA
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 2.5mA$	5.0	6.0	7.0	V
		$I_C = 50A, V_{GE} = 15V,$				
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	T <sub>j</sub> = 25°C	-	1.65	2.10	V
		T <sub>j</sub> = 175°C	-	2.15	-	V

# ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

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Parameter Symbol		Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V,	-	1568	-	
Output Capacitance	$C_oes$	V <sub>GE</sub> = 0V,	-	134	-	pF
Reverse transfer Capacitance	$C_{res}$	f = 1MHz	-	23	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 300V,	-	58	-	
Gate - Emitter Charge	$Q_ge$	I <sub>C</sub> = 50A,	-	15	-	nC
Gate - Collector Charge	$Q_gc$	V <sub>GE</sub> = 15V	-	24	-	
Turn - on Delay Time	t <sub>d(on)</sub>		-	36	-	
Rise Time	t <sub>r</sub>	$I_C = 50A, V_{CC} = 400V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	21	-	
Turn - off Delay Time	t <sub>d(off)</sub>	$T_i = 25^{\circ}C$	-	115	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	91	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> include diode reverse recovery	-	1.46	-	mJ
Turn - off Switching Loss	E <sub>off</sub>	,	-	1.29	-	
Turn - on Delay Time	t <sub>d(on)</sub>		-	37	-	
Rise Time	t <sub>r</sub>	$I_C = 50A, V_{CC} = 400V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	33	-	ns
Turn - off Delay Time	t <sub>d(off)</sub>	$T_i = 175^{\circ}C$	-	145	-	
Fall Time	t <sub>f</sub>	Inductive Load	-	147	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> include diode reverse recovery	-	1.97	-	m l
Turn - off Switching Loss	E <sub>off</sub>		-	1.85	-	mJ
Reverse Bias		$I_{\rm C}$ = 150A, $V_{\rm CC}$ = 520V,			-	
Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V,$	FULL SQUARE			
		$R_G = 50\Omega, T_j = 175^{\circ}C$				
Short Circuit Withstand Time	t <sub>sc</sub>	$V_{CC} \le 360V$ , $V_{GE} = 15V$ , $T_j = 25^{\circ}C$	8	-	-	μs
Short Circuit Withstand Time	t <sub>sc</sub> *2	$V_{CC} \le 360V$ , $V_{GE} = 15V$ , $T_j = 150$ °C	6	-	-	μs

<sup>\*2</sup> Design assurance without measurement

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## • Electrical Characteristic Curves

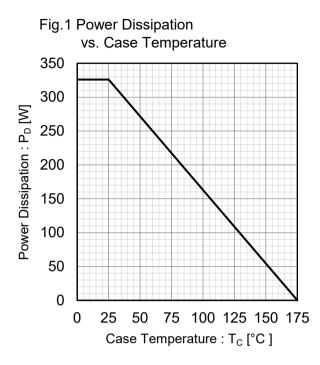


Fig.2 Collector Current vs. Case Temperature

100

80

40  $T_{j \leq 175^{\circ}C}$   $T_{j \leq 15V}$ 0

25

50

75

100

125

150

175

Case Temperature:  $T_{c}$  [°C]

Fig.3 Forward Bias Safe Operating Area

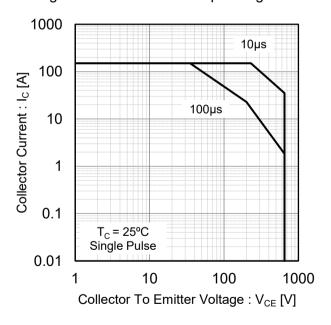
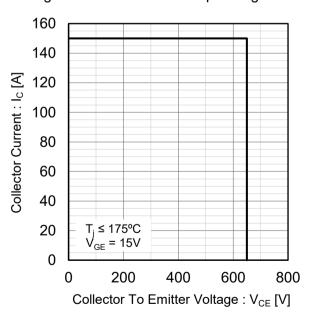


Fig.4 Reverse Bias Safe Operating Area



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## • Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

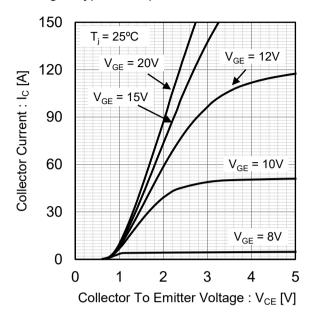


Fig.6 Typical Output Characteristics

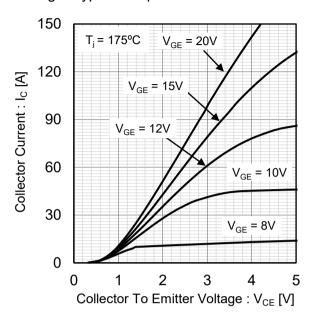


Fig.7 Typical Transfer Characteristics

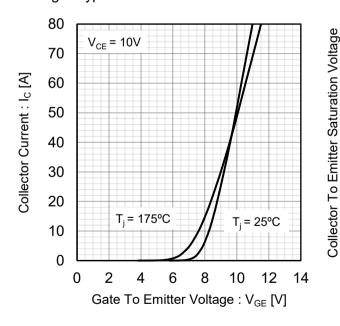
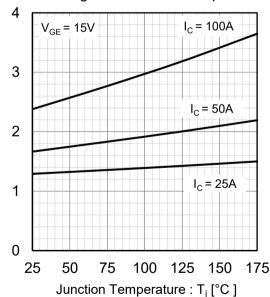


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



: V<sub>CE(sat)</sub> [V]

#### Electrical Characteristic Curves

Voltage vs. Gate To Emitter Voltage 20 Collector To Emitter Saturation Voltage  $T_{i} = 25^{\circ}C$ 15 100A  $: V_{CE(sat)}[V]$  $I_C = 50A$ 10 I<sub>C</sub> = 25A 5 0

10

15

Gate To Emitter Voltage: VGE [V]

Fig.9 Typical Collector To Emitter Saturation

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

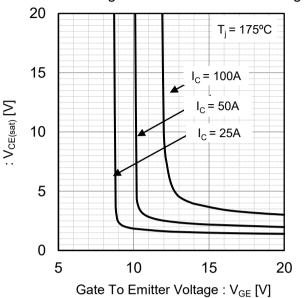


Fig.11 Typical Switching Time vs. Collector Current

5

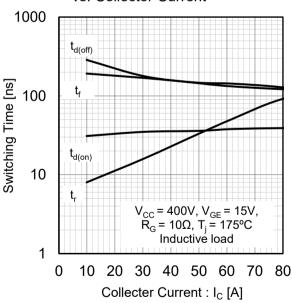
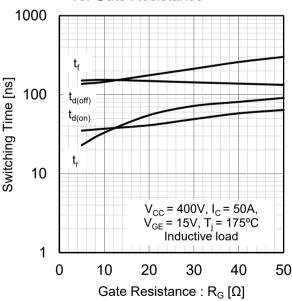


Fig.12 Typical Switching Time vs. Gate Resistance



Collector To Emitter Saturation Voltage

20

## ● Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

10

| Eof | V<sub>CC</sub> = 400V, V<sub>GE</sub> = 15V, R<sub>G</sub> = 10Ω, T<sub>j</sub> = 175°C | Inductive load | O 10 20 30 40 50 60 70 80 | Collector Current : I<sub>C</sub> [A]

Fig.14 Typical Switching Energy Losses vs. Gate Resistance 10 Switching Energy Losses [mJ]  $E_{off}$ 1 0.1  $V_{CC} = 400V, I_C = 50A,$   $V_{GE} = 15V, T_j = 175^{\circ}C$ Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000  $\boldsymbol{C}_{\text{ies}}$ 1000 Capacitance [pF]  $\mathsf{C}_\mathsf{oes}$ 100 10  $C_{res}$ f = 1MHz  $V_{GE} = 0V$  $T_i = 25^{\circ}C$ 1 0.01 0.1 10 100 Collector To Emitter Voltage: V<sub>CE</sub> [V]

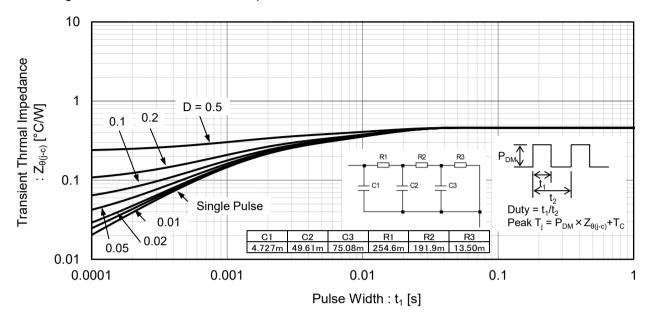
15 V<sub>CE</sub> = 200V Gate To Emitter Voltage : V<sub>GE</sub> [V] V<sub>CE</sub> = 300V 10 V<sub>CE</sub> = 400V 5  $I_{\rm C} = 50A$  $T_i = 25^{\circ}C$ 0 0 10 20 30 40 50 60 Gate Charge: Qq [nQ]

ROHM

Fig.16 Typical Gate Charge

## • Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



ROHM

## ●Inductive Load Switching Circuit and Waveform

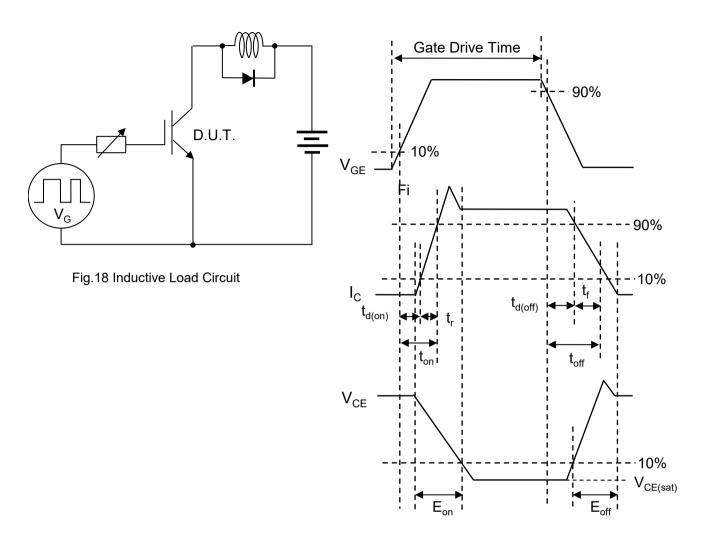


Fig.19 Inductive Load Waveform

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